

CONTACT PROCESS AND STRUCTURE FOR A SEMICONDUCTOR DEVICE

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ABSTRACT OF THE DISCLOSURE

A contact process for a semiconductor device containing
a base region of a first conductivity type formed on a
10 semiconductor substrate comprises formation of a first shallow
layer of the first conductivity type on the base region, deposition of
an insulator on the first shallow layer, etching the insulator and
first shallow layer to form a contact hole, thermally driving the first
shallow layer more deeply into said base region, formation of a
15 second shallow layer of a second conductivity type on the base
region at the bottom of the contact hole, filling a metal in the
contact hole to contact the sidewall of the first shallow layer and
the second shallow layer.